

Wang et al
FET HAVING EPITAXIAL SILICON GROWTH
Atty. Docket 400.147US01

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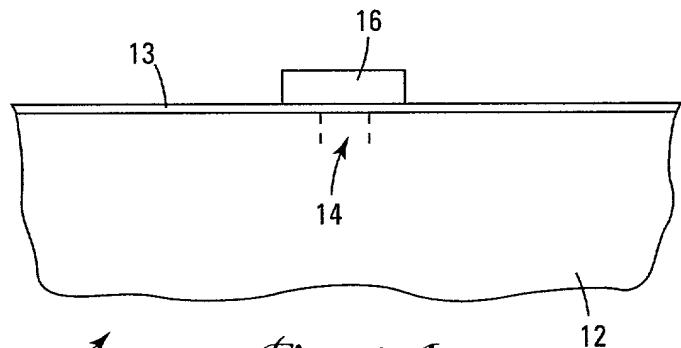


Fig. 1A

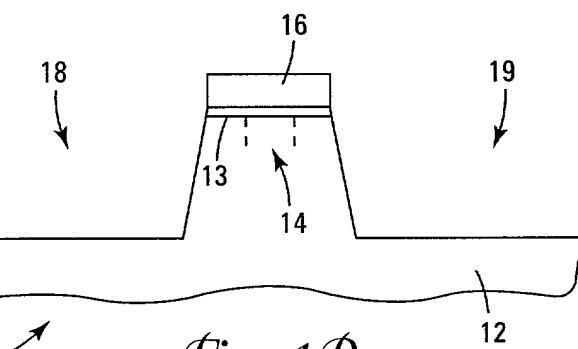


Fig. 1B

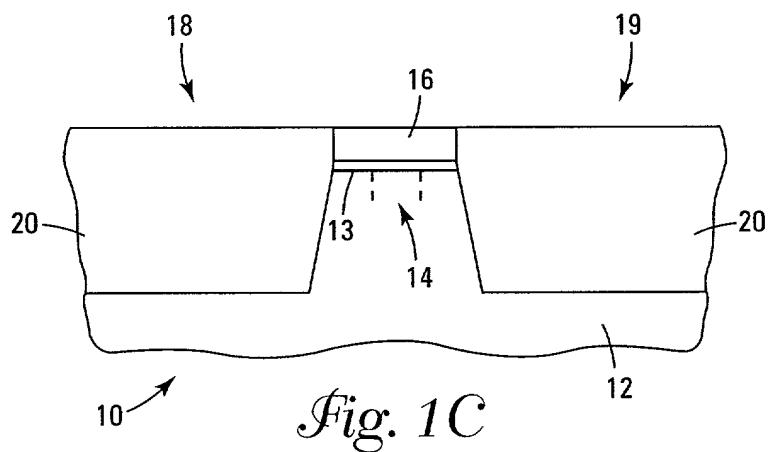


Fig. 1C

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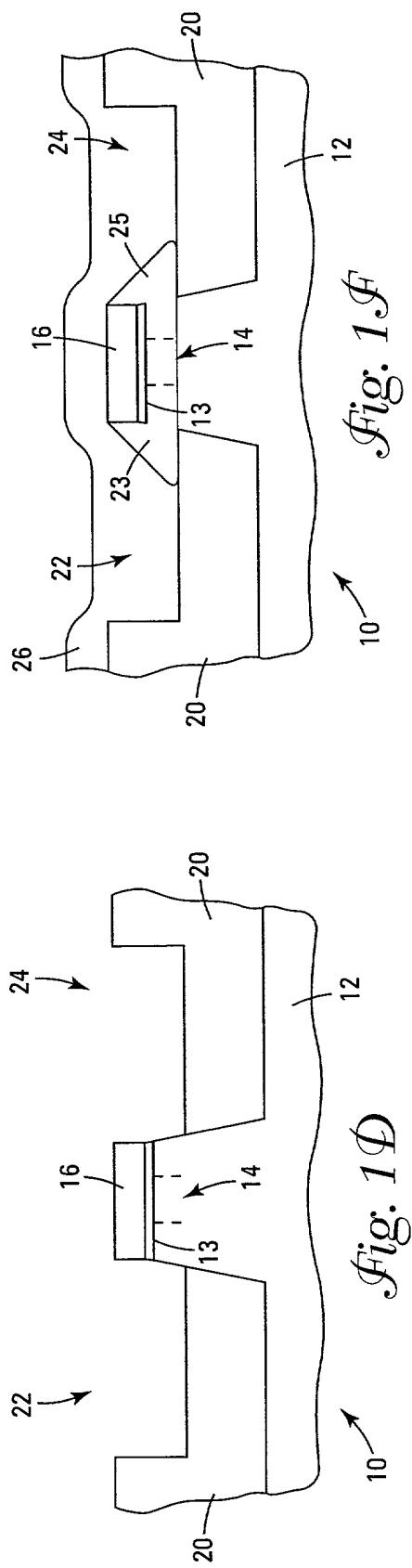


Fig. 1D

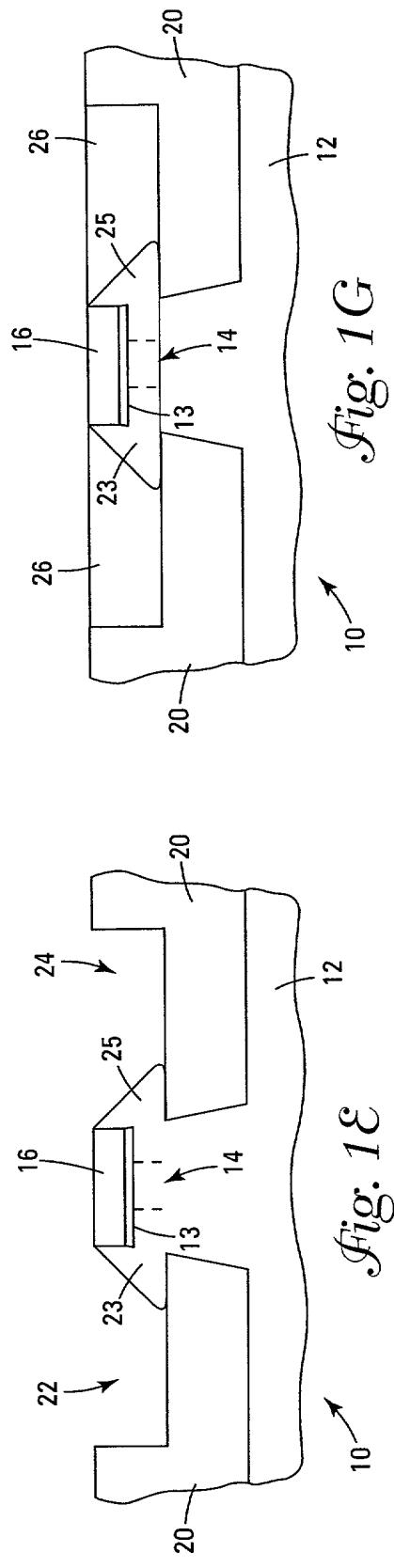


Fig. 1E

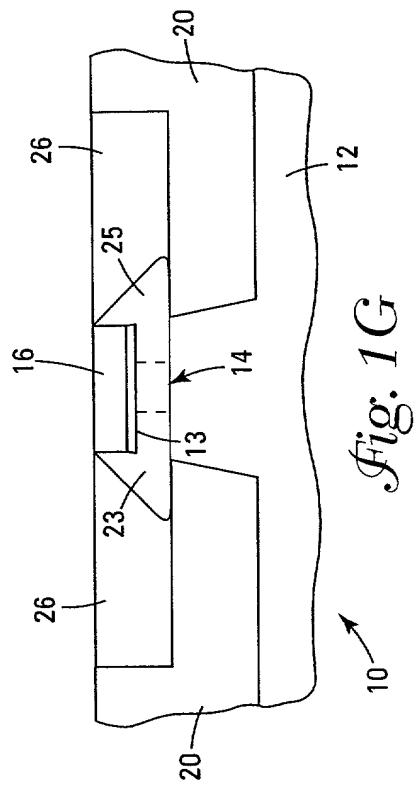


Fig. 1F

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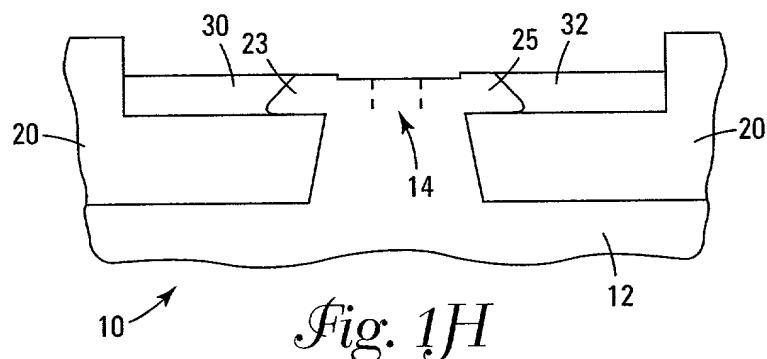


Fig. 1H

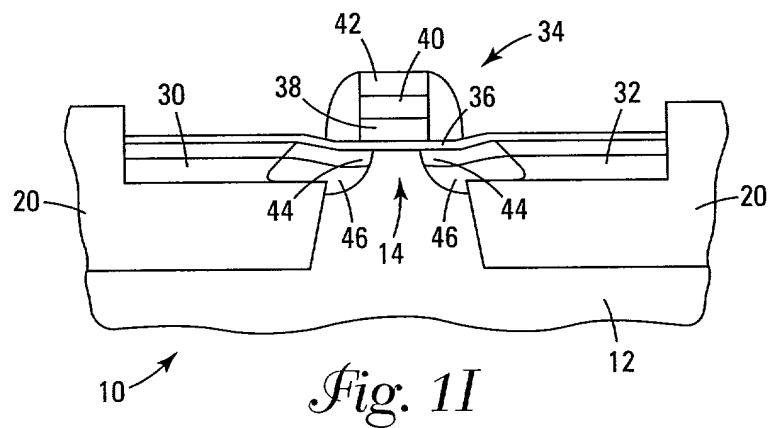


Fig. 1I

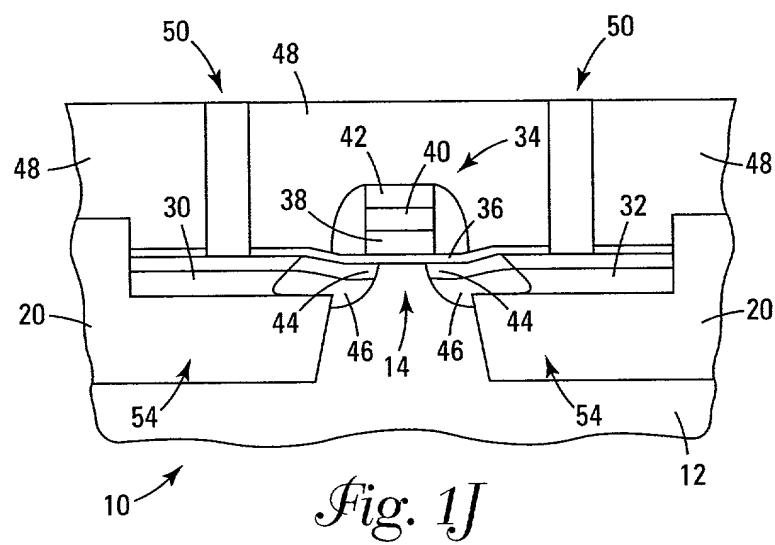


Fig. 1J

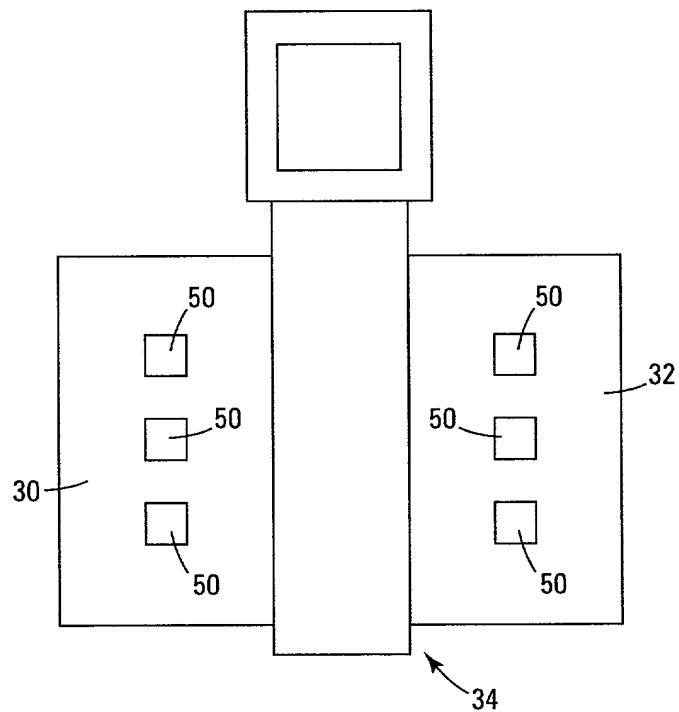


Fig. 2

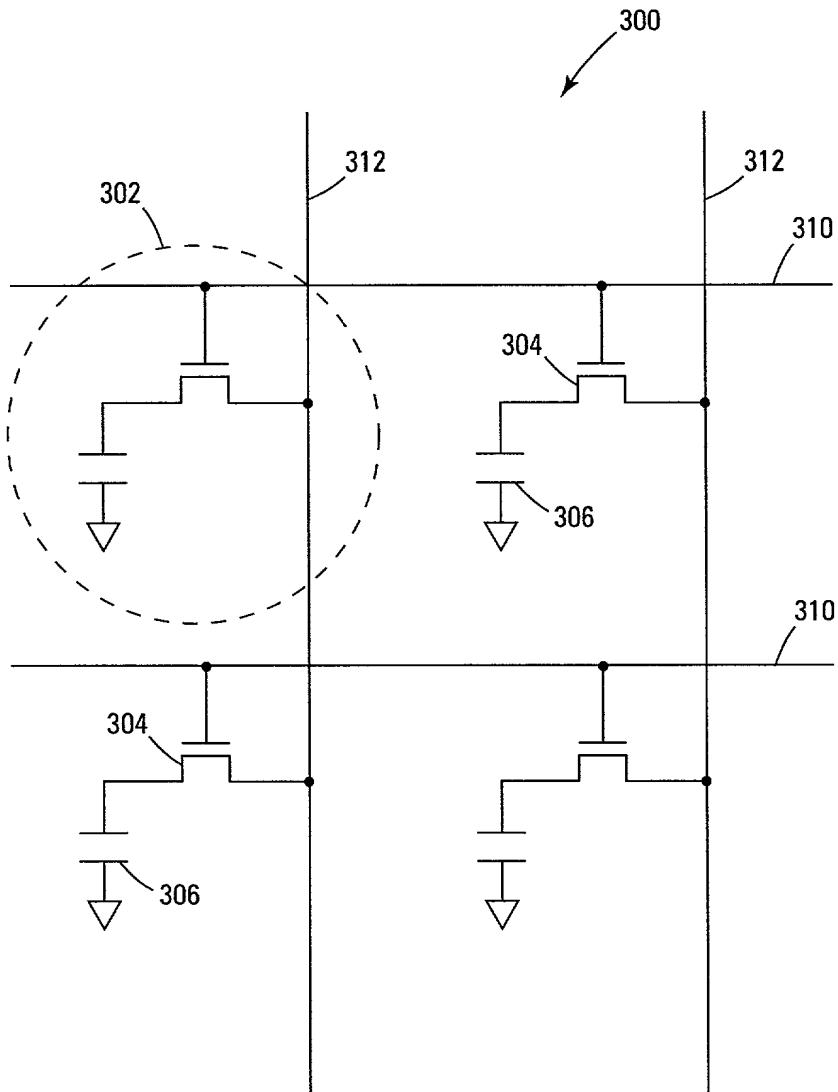


Fig. 3

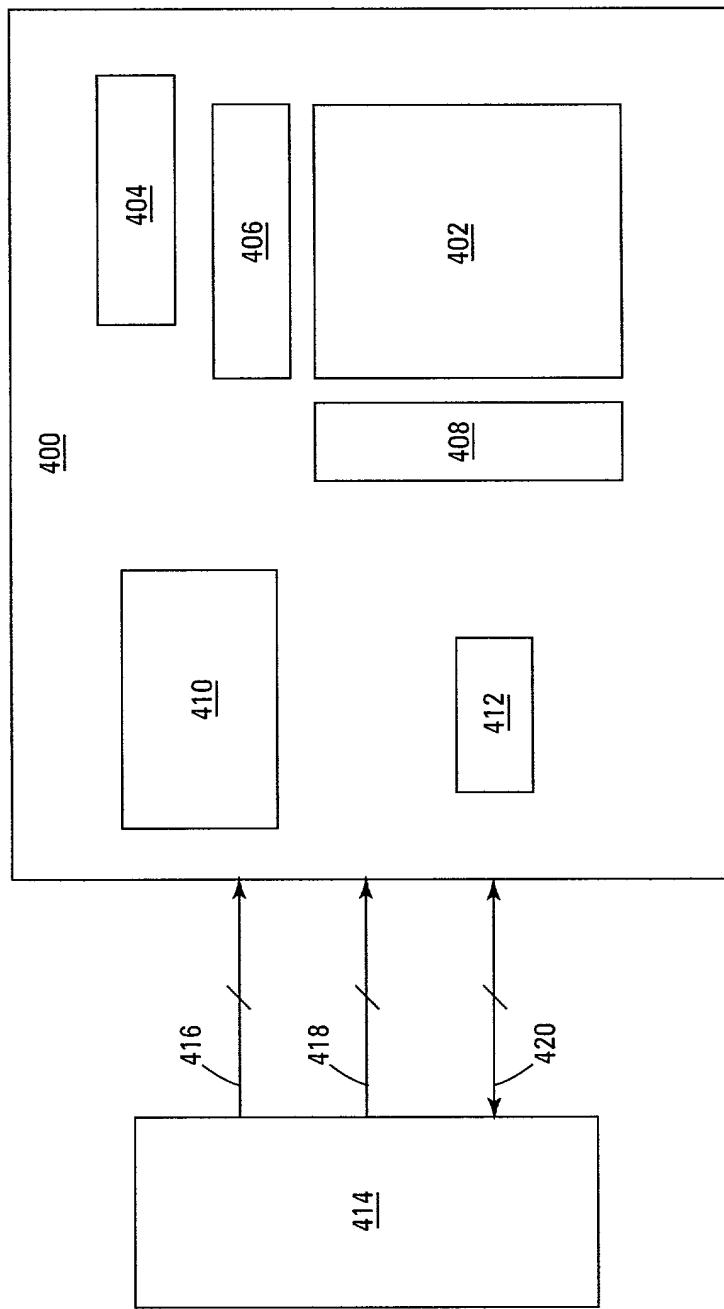


Fig. 4